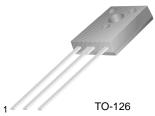


### BD439/441

# Medium Power Linear and Switching Applications

Complement to BD440, BD442 respectively



# **NPN Epitaxial Silicon Transistor**

1. Emitter 2.Collector 3.Base

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: BD439	60	V
	: BD441	80	V
V <sub>CES</sub>	Collector-Emitter Voltage		
	: BD439	60	V
	: BD441	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BD439	60	V
	: BD441	80	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	4	Α
I <sub>CP</sub>	*Collector Current (Pulse)	7	Α
I <sub>B</sub>	Base Current	1	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	36	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

### **Electrical Characteristics** $T_C=25$ °C unless otherwise noted

Symbol	Paramete	er	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaining	ng Voltage : BD439	I <sub>C</sub> = 100mA, I <sub>B</sub> = 0	60			V
		: BD441	.С, .В	80			V
I <sub>CBO</sub>	Collector Cut-off Current	: BD439	$V_{CB} = 60V, I_{E} = 0$			100	μΑ
		: BD441	$V_{CB} = 80V, I_{E} = 0$			100	μΑ
I <sub>CES</sub>	Collector Cut-off Current	: BD439	$V_{CE} = 60V, V_{BE} = 0$			100	μΑ
		: BD441	$V_{CE} = 80V, V_{BE} = 0$			100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current		$V_{EB} = 5V, I_{C} = 0$			1	mΑ
h <sub>FE</sub>	* DC Current Gain	: BD439	$V_{CE} = 5V, I_{C} = 10mA$	20	130		
		: BD441		15	130		
		: BD439	$V_{CE} = 1V, I_{C} = 500 \text{mA}$	40	140		
		: BD441		40	140		
		: BD439	$V_{CE} = 1V, I_{C} = 2A$	25			
		: BD441		15			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation	on Voltage	$I_C = 2A, I_B = 0.2A$			0.8	V
V <sub>BF</sub> (on)	* Base-Emitter ON Voltage		$V_{CE} = 5V, I_{C} = 10mA$		0.58		V
'			$V_{CE} = 1V, I_{C} = 2A$			1.5	V
f⊤	Current Gain Bandwidth Pr	roduct	$V_{CF} = 1V, I_{C} = 250 \text{mA}$	3			MH:

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# **Typical Characteristics**

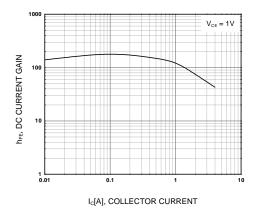


Figure 1. DC current Gain

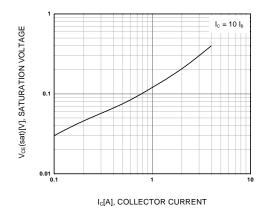


Figure 2. Collector-Emitter Saturation Voltage

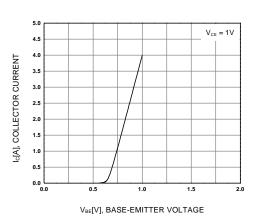


Figure 3. Base-Emitter On Voltage

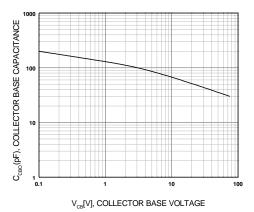


Figure 4. Collector-Base Capacitance

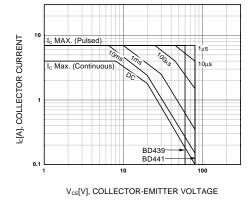


Figure 5. Safe Operating Area

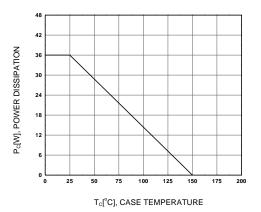
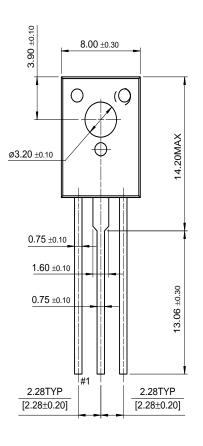


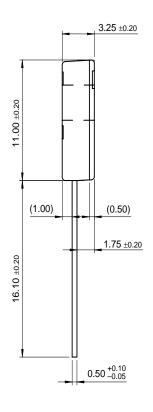
Figure 6. Power Derating

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# **Package Demensions**

TO-126







Dimensions in Millimeters

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DenseTrench™	GTO™	QFET™	TinyLogic™
DOME™	HiSeC™	QS™	UHC™
EcoSPARK™	ISOPLANAR™	QT Optoelectronics™	UltraFET <sup>®</sup>
E <sup>2</sup> CMOS <sup>™</sup>	LittleFET™	Quiet Series™	VCX™
EnSigna™	MicroFET™	SLIENT SWITCHER®	
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Rev. H2

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